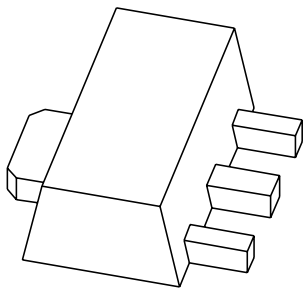


DATA SHEET



BSR40; BSR41; BSR42; BSR43 NPN medium power transistors

Product data sheet
Supersedes data of 1999 Apr 28

2004 Dec 13

NPN medium power transistors

**BSR40; BSR41;
BSR42; BSR43**

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

- Thick and thin-film circuits
- Telephony and general industrial applications.

DESCRIPTION

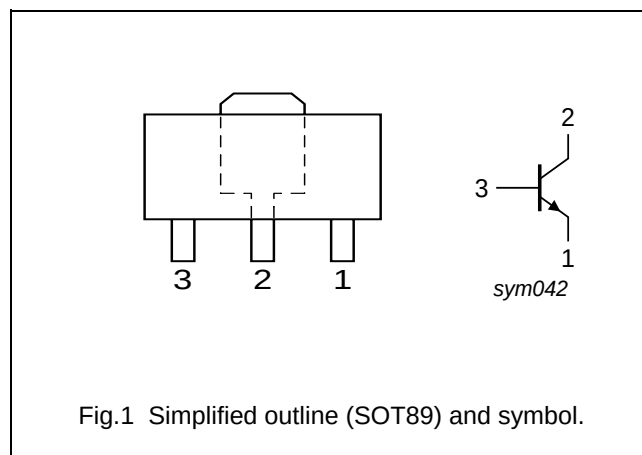
NPN medium power transistor in a SOT89 plastic package. PNP complements: BSR30; BSR31 and BSR33.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BSR40	AR1	BSR42	AR3
BSR41	AR2	BSR43	AR4

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSR40	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89
BSR41			
BSR42			
BSR43			

NPN medium power transistors

BSR40; BSR41; BSR42;
BSR43

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BSR40; BSR41		–	70	V
	BSR42; BSR43		–	90	V
V _{CEO}	collector-emitter voltage	open base			
	BSR40; BSR41		–	60	V
	BSR42; BSR43		–	80	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	2	A
I _{BM}	peak base current		–	0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.35	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	ambient temperature		–65	+150	°C

Note

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm².
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	93	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		13	K/W

Note

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm².
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

NPN medium power transistors

BSR40; BSR41; BSR42;
BSR43

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0\text{ A}; V_{CB} = 60\text{ V}$	–	100	nA
		$I_E = 0\text{ A}; V_{CB} = 60\text{ V}; T_j = 150\text{ °C}$	–	50	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0\text{ A}; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; \text{note 1}$	10 30	– –	
	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; \text{note 1}$	40 100	120 300	
	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; \text{note 1}$	30 50	– –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	250	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.2	V
C_c	collector capacitance	$I_E = I_C = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	12	pF
C_e	emitter capacitance	$I_C = I_E = 0\text{ A}; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	90	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	–	MHz
Switching times (between 10% and 90% levels)					
t_{on}	turn-on time	$I_{Con} = 100\text{ mA}; I_{Bon} = 5\text{ mA};$ $I_{Boff} = -5\text{ mA}$	–	250	ns
t_{off}	turn-off time		–	1	μs

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.01$.

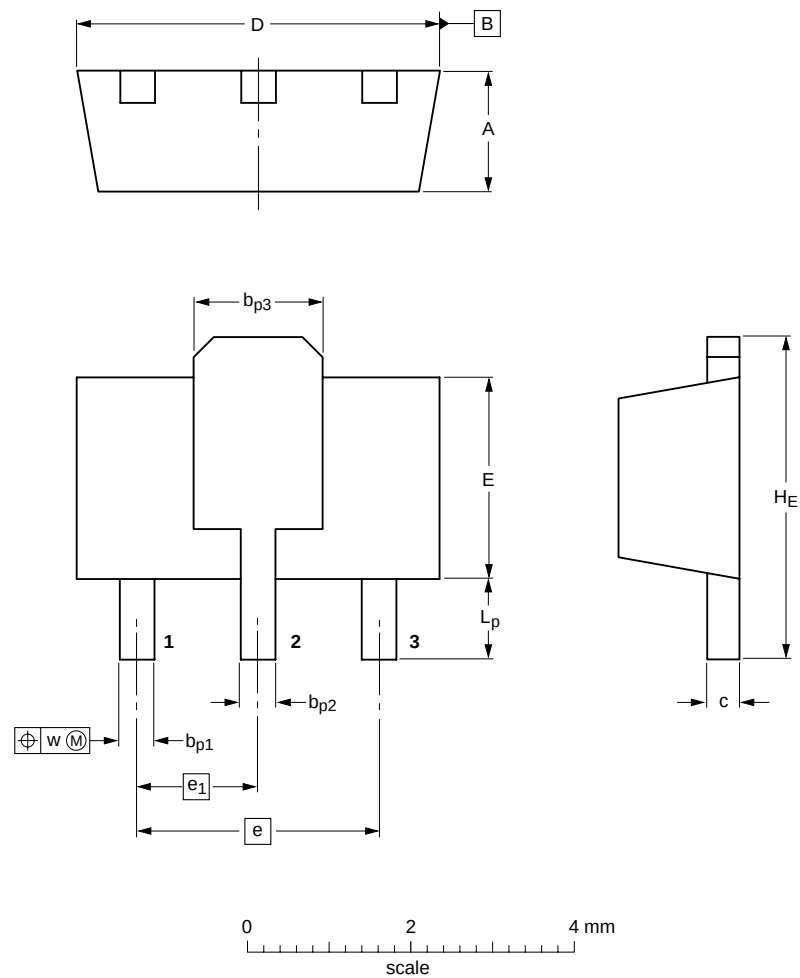
NPN medium power transistors

BSR40; BSR41; BSR42;
BSR43

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	bp1	bp2	bp3	c	D	E	e	e1	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT89		TO-243	SC-62			04-08-03 06-03-16